**INFORMATION DISCLOSURE CITATION***(Use several sheets if necessary)*

Docket Number (Optional)

BREV 12370 CON4

Application Number

10/784,601

Applicant(s)

ASPAR et al.

Filing Date

February 23, 2004

Group Art Unit

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
G		SU 1282757	12.30.83	RUSSIA	H01L	21/265		

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				Applicant(s) ASPAR et al.			
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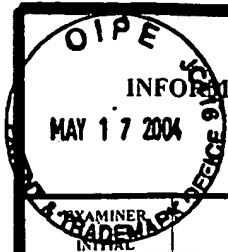
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G		Reissue App. 10/449,786					

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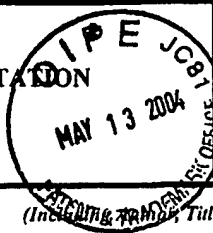
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D.B. Courts FOURSON

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	EP 0703 609	3/27/96	EPO			✓	
	0 660 140	6/28/95	EPO			✓	
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FORM PTO-1449	SERIAL NO. 10/784601	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE	GROUP ART UNIT 2823
(use several sheets if necessary)	APPLICANT(S): Aspar et al.	

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APPLICANT(S):		Aspar et al.

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<i>DRC</i>	A9	2725074	3/29/96	France			X
<i>G</i>	A10	0355913	2/28/90	EPO		X	
<i>G</i>	A11	0504714	9/23/92	EPO		X	

EXAMINER INITIAL		OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)
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<i>G</i>	A13	Aspar et al., SMART-CUT®: The basic fabrication process for UNIBOND® SOI wafers, <i>SEMI</i> 1996, pp. 37-46
<i>G</i>	A14	Klem et al., Characteristics of lift-off fabricated AlGaAs/InGaAs single-strained quantum well structures on glass and silicon substrates, <i>Inst. Phys. Conf.</i> , Ser. No 96: Chapter 6, pp. 387-392
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<i>JE</i>	5,034,343	07/23/1991	ROUSE ET AL	437	86	
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						YES	NO
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<i>Dae</i>	59-54217	03/29/1984	JAPAN	H01L	21/20		✓

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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

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<p><i>D.M. Collins</i> <i>Ferguson</i></p>		<p><i>12-21-01</i> <i>7/17/05</i></p>

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EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G-DAC	5 3 7 4 5 6 4	12/20/94	Bruel	437	24	
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